

SANYO

No.3706A

2SC4637

NPN Triple Diffused Planar Silicon Transistor
 High-Voltage Amp,
 High-Voltage Switching Applications

Features

- High breakdown voltage (V_{CEO} min = 1800V).
- Small Cob (typical Cob = 1.8pF).
- Full-isolation package.
- High reliability (Adoption of HVP process).

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

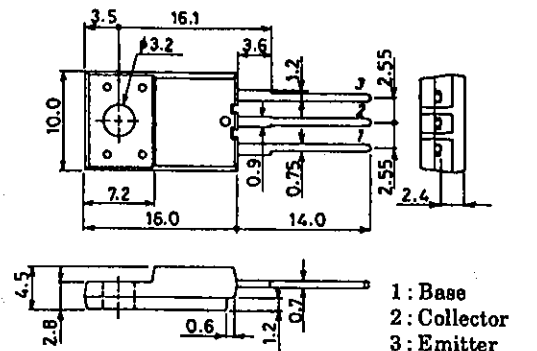
			unit
Collector-to-Base Voltage	V_{CBO}	2000	V
Collector-to-Emitter Voltage	V_{CEO}	1800	V
Emitter-to-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	15	mA
Collector Current (Pulse)	I_{CP}	50	mA
Collector Dissipation	P_C	2	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 1800\text{V}, I_E = 0$			1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$			1	μA
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 300\mu\text{A}$	10		60	
Gain-Bandwidth Product	f_T	$V_{CE} = 10\text{V}, I_C = 300\mu\text{A}$		6		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 600\mu\text{A}, I_B = 120\mu\text{A}$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 600\mu\text{A}, I_B = 120\mu\text{A}$			2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	2000			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 100\mu\text{A}, R_{BE} = \infty$	1800			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	5			V
Output Capacitance	Cob	$V_{CB} = 100\text{V}, f = 1\text{MHz}$		1.8		pF
Thermal Resistance	R_{thj-c}	Junction - case			8.3	$^\circ\text{C/W}$

Package Dimensions 2079B

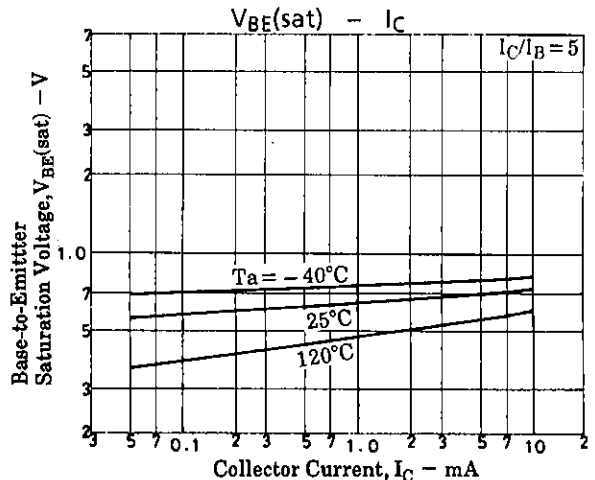
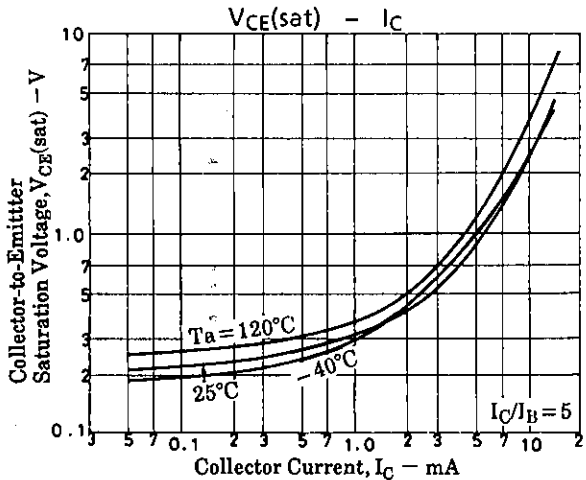
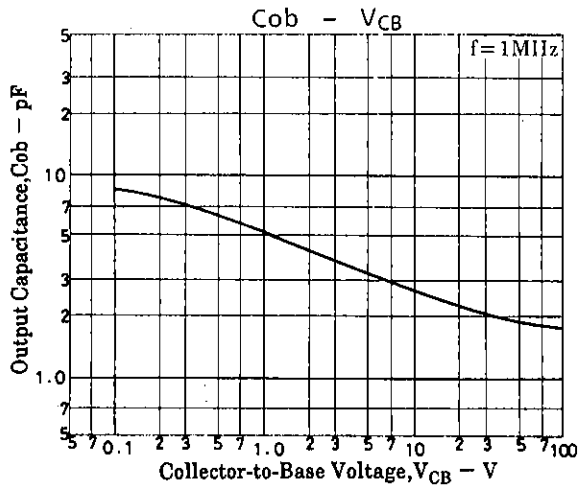
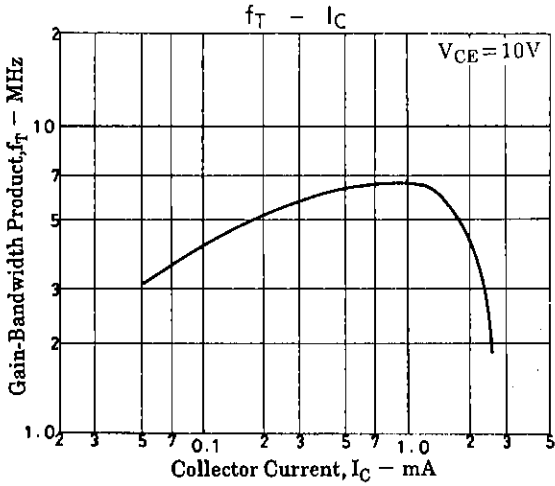
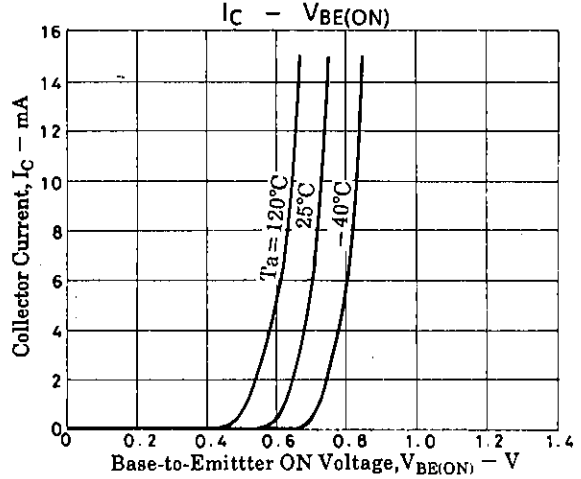
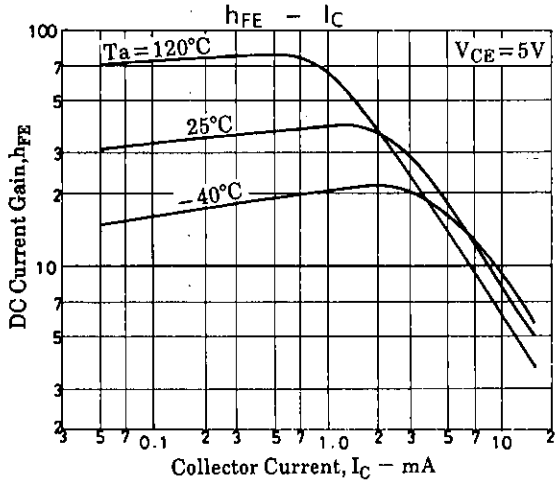
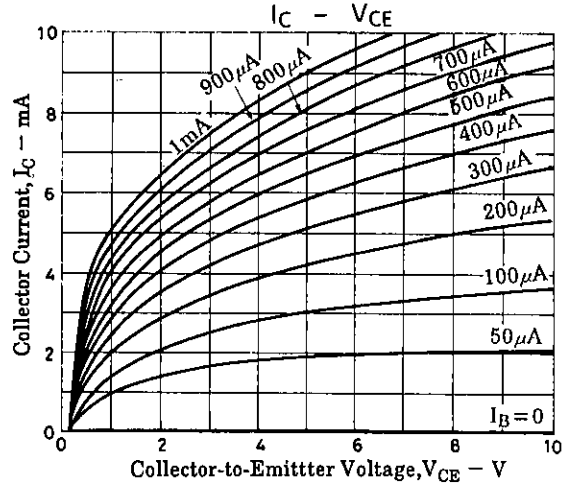
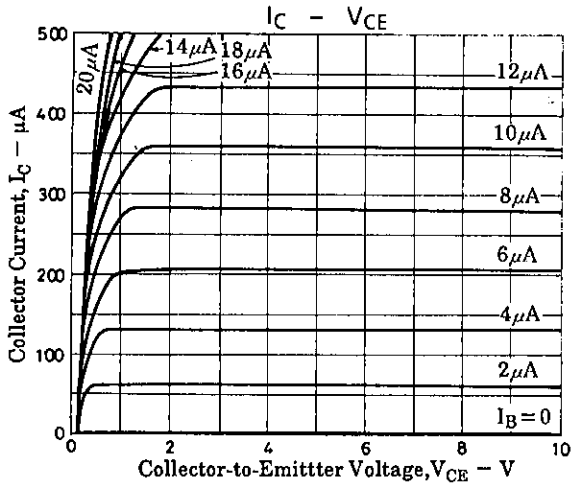
(unit : mm)

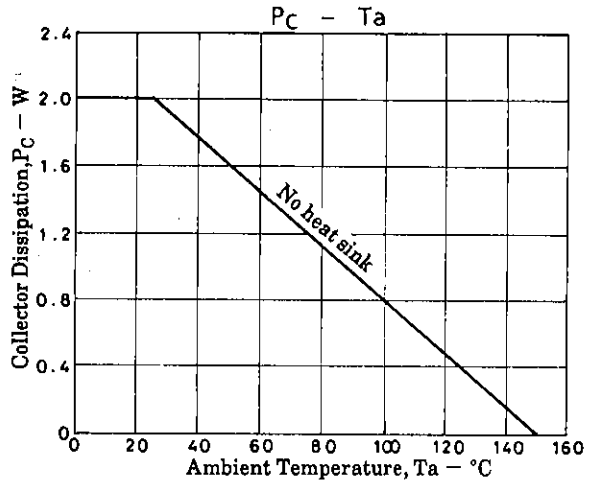
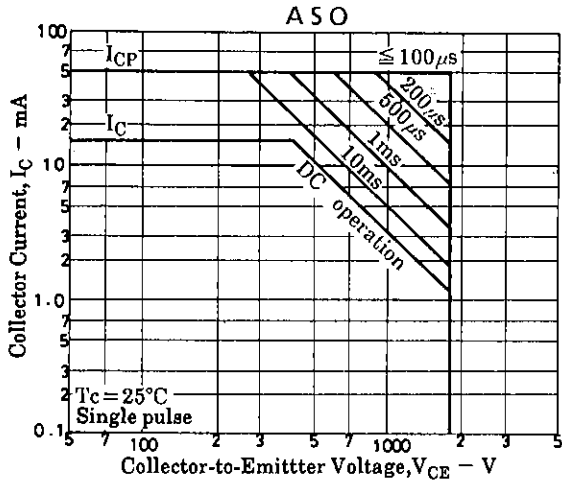


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